AMENDMENTS TO THE SPECIFICATION:

Please replace the paragraph beginning on page 6, line 10 with the following amended paragraph:

As shown in Figure 2(a), a low K dielectric layer 20 is formed above a semiconductor 10. Any number of intervening layers can be formed between the semiconductor 10 and the low K dielectric layer 20. Some of these intervening layers will include metal lines and ~~addition~~ additional dielectric layers. Electronic devices such as transistors, diodes, etc. will be formed in the semiconductor 10 and have been omitted from all the Figures for clarity. Low K dielectric material used to form layer 20 is defined for purposes of this invention as a dielectric material with a dielectric constant of approximately $\leq$ 3.7. The term low K dielectric is also intended to include dielectric material with a dielectric constant of $\leq$ 3.2. The term low K dielectric is also intended to include the class of ultra-low K dielectric material which is defined as dielectric material with a dielectric constant of $\leq$ 2.5. Various embodiments of the instant invention can include the following low K and ultra-low K dielectric materials: silsesquioxane (SSQ)-based materials, e.g., methysilsesquioxane (MSQ), or hydrogensilsesquioxane (HSQ), silica-based materials, e.g., carbon- or fluorine- doped silica glasses, organic-polymer-based materials, amorphous-carbon-based materials, and any other dielectric material that can be made with porous characteristics to reduce the dielectric constant. In general low K dielectric material has pores that can be described as open spaces within the dielectric material. In an embodiment the pores in the low K dielectric layer can comprise an average pore size (or pore diameter) of 1nm or larger. In a further

embodiment the pores in the low K dielectric layer can comprise an average pore size (or pore diameter) of 2nm or larger.